



Docket No.: M4065.0227/P227  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Tongbi Jiang, et al.

Application No.: 09/652,216

Group Art Unit: 2813

Filed: August 30, 2000

Examiner: E. Pert

For: METHOD AND APPARATUS FOR  
REDUCING SUBSTRATE BIAS VOLTAGE  
DROP

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15 steps to  
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AMENDMENT

Box Non-Fee Amendment  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

In response to the Office Action dated December 21, 2001 (Paper No. 5),  
please amend the above-identified U.S. Patent application as follows:

In the Specification:

Please rewrite the paragraph beginning on page 2, line 3 as follows:

It is known in the art to maintain a stable substrate bias voltage  $V_{bb}$  over a large area of the substrate by spacing the well plugs close together, however this occupies large substrate real estate. It is also known to use a heavily doped substrate with a lightly doped epitaxial layer to help stabilize the substrate voltage; however such processes are expensive. It would be desirable to have a semiconductor device and method of making the same that cost effectively reduces bias voltage  $V_{bb}$  drop across the substrate, and which also reduces

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cont

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